

FGPF4536

360 V PDP Trench IGBT

Features

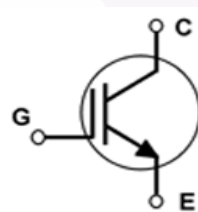
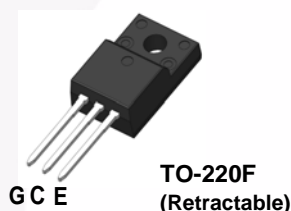
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.59 \text{ V @ } I_C = 50 \text{ A}$
- High Input Impedance
- Fast Switching
- RoHS Compliant

Applications

- PDP TV, Consumer appliances, Lighting

General Description

Using novel trench IGBT technology, Fairchild's new series of trench IGBTs offer the optimum performance for consumer appliances, PDP TV and lighting applications where low conduction and switching losses are essential.



Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
V_{CES}	Collector to Emitter Voltage	360	V
V_{GES}	Gate to Emitter Voltage	± 30	V
$I_{C \text{ pulse}(1)*}$	Pulsed Collector Current @ $T_C = 25^\circ\text{C}$	220	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	28.4	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	11.4	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction to Case	-	4.4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	62.5	$^\circ\text{C/W}$

Notes:

(1) Half Sine Wave, $D < 0.01$, pulse width $< 1 \mu\text{sec}$

* $I_{C \text{ pulse}}$ limited by max T_J

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGPF4536	FGPF4536	TO-220F	Tube	N/A	N/A	50

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{CES}	Collector to Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 250 μA	360	-	-	V
ΔBV _{CES} / ΔT _J	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0V, I _C = 250 μA	-	0.4	-	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0 V	-	-	100	μA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0 V	-	-	±400	nA
On Characteristics						
V _{GE(th)}	G-E Threshold Voltage	I _C = 250 μA, V _{CE} = V _{GE}	2.4	3.3	4.0	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 20 A, V _{GE} = 15 V	-	1.19	-	V
		I _C = 30 A, V _{GE} = 15 V	-	1.33	-	V
		I _C = 50 A, V _{GE} = 15 V, T _C = 25°C	-	1.59	1.8	V
		I _C = 50 A, V _{GE} = 15 V, T _C = 125°C	-	1.66	-	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} = 30 V, V _{GE} = 0 V, f = 1MHz	-	1295	-	pF
C _{oes}	Output Capacitance		-	56	-	pF
C _{res}	Reverse Transfer Capacitance		-	43	-	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{CC} = 200 V, I _C = 20 A, R _G = 5 Ω, V _{GE} = 15 V, Resistive Load, T _C =25°C	-	5	-	ns
t _r	Rise Time		-	20	-	ns
t _{d(off)}	Turn-Off Delay Time		-	41	-	ns
t _f	Fall Time		-	182	-	ns
t _{d(on)}	Turn-On Delay Time	V _{CC} = 200 V, I _C = 20 A, R _G = 5 Ω, V _{GE} = 15 V, Resistive Load, T _C = 125°C	-	4.6	-	ns
t _r	Rise Time		-	21	-	ns
t _{d(off)}	Turn-Off Delay Time		-	43	-	ns
t _f	Fall Time		-	249	-	ns
Q _g	Total Gate Charge	V _{CE} = 200 V, I _C = 20 A, V _{GE} = 15 V	-	47	-	nC
Q _{ge}	Gate to Emitter Charge		-	5.4	-	nC
Q _{gc}	Gate to Collector Charge		-	15	-	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

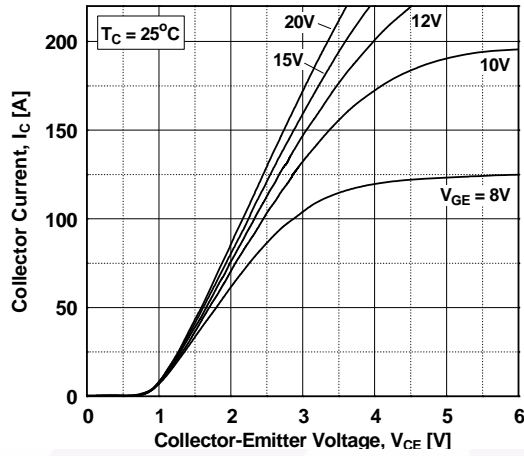


Figure 2. Typical Output Characteristics

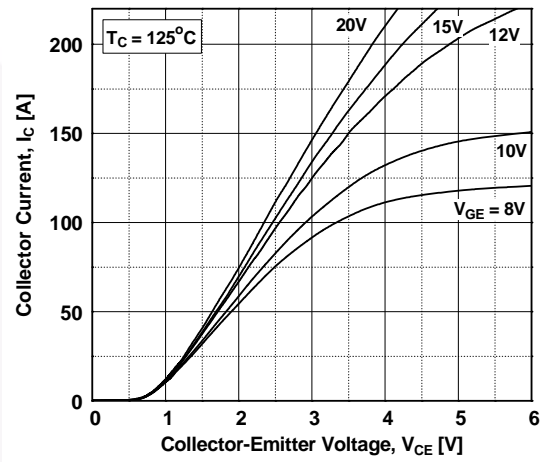


Figure 3. Typical Saturation Voltage Characteristics

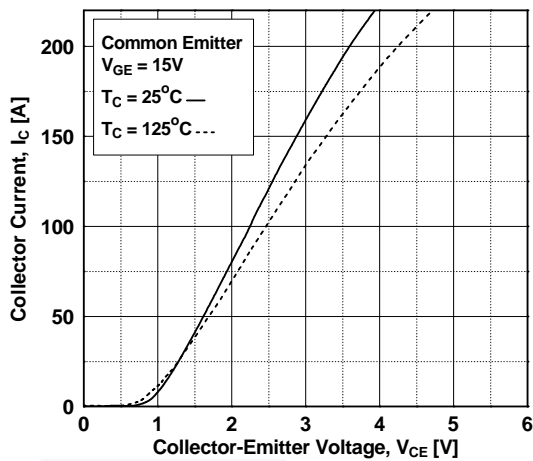


Figure 4. Transfer Characteristics

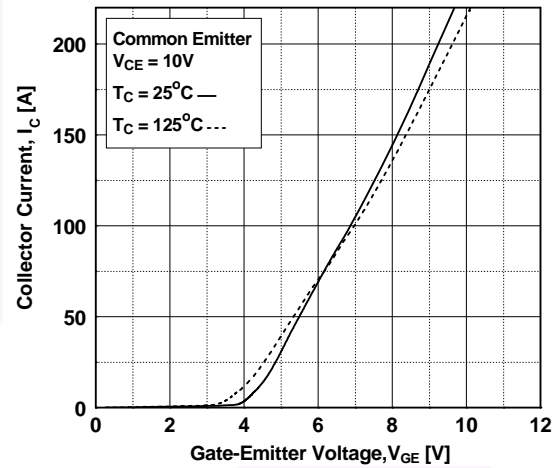


Figure 5. Saturation Voltage vs. V_{GE}

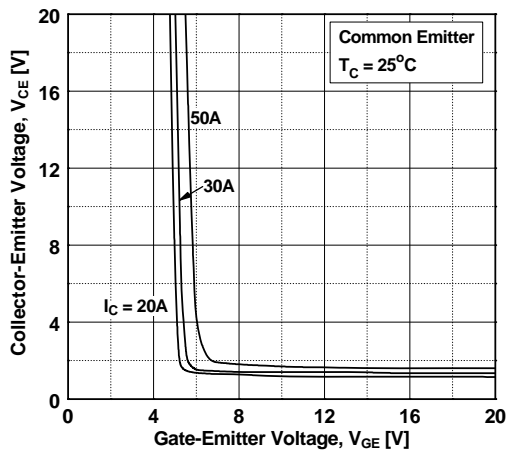
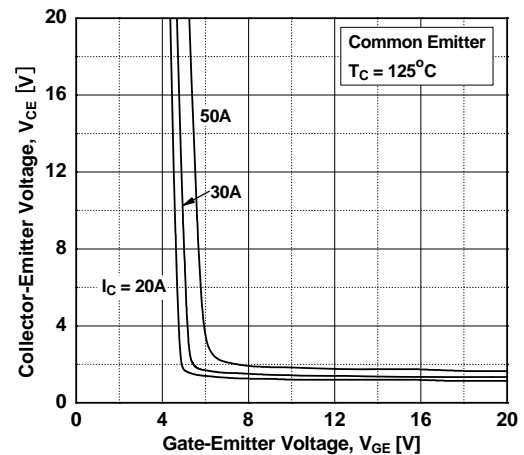


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. Case Temperature at Variant Current Level

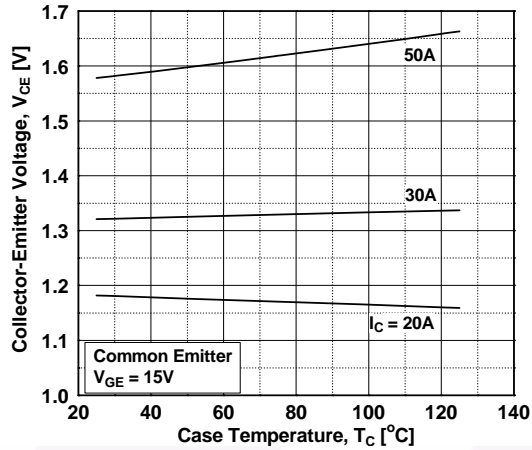


Figure 8. Capacitance Characteristics

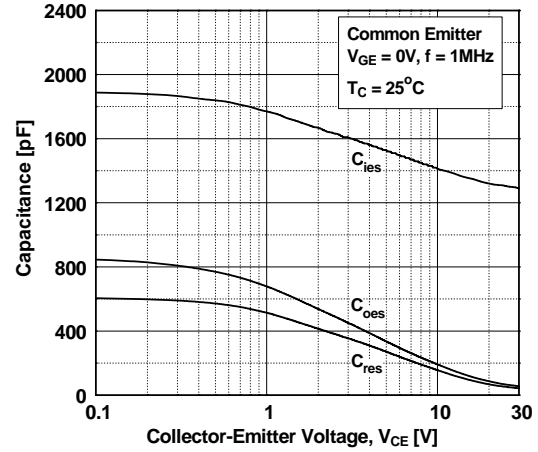


Figure 9. Gate charge Characteristics

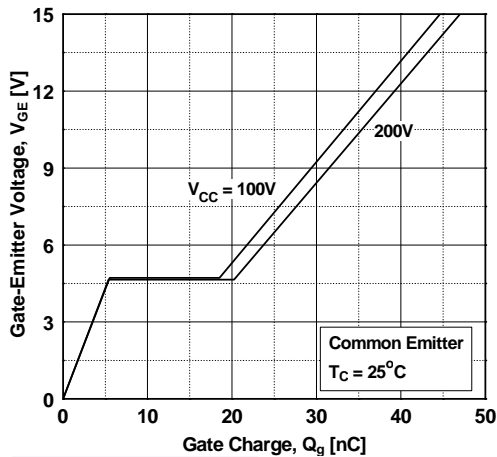


Figure 10. SOA Characteristics

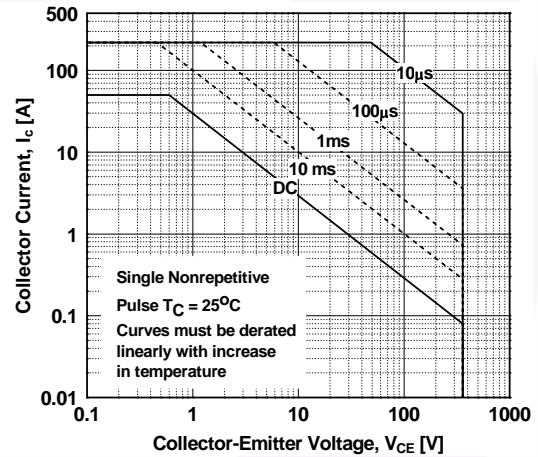


Figure 11. Turn-on Characteristics vs. Gate Resistance

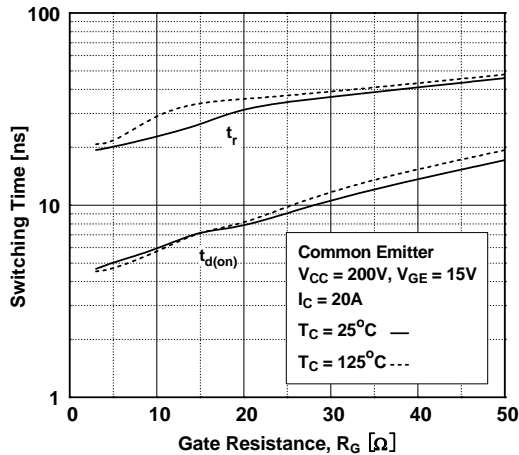
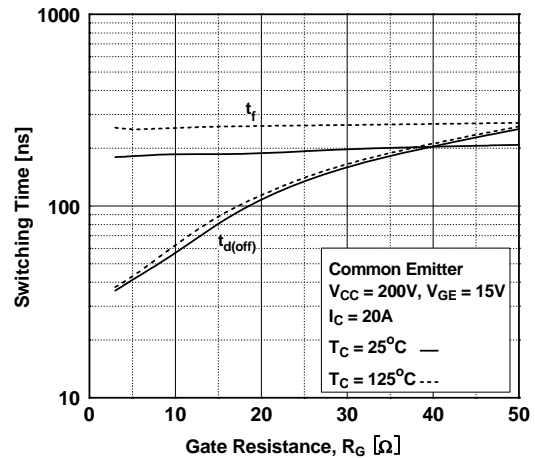


Figure 12. Turn-off Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-on Characteristics vs. Collector Current

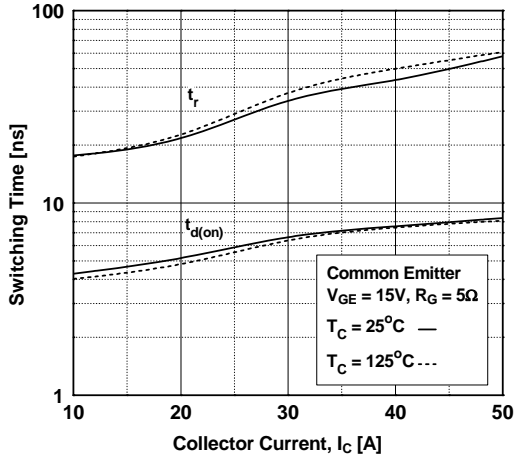


Figure 14. Turn-off Characteristics vs. Collector Current

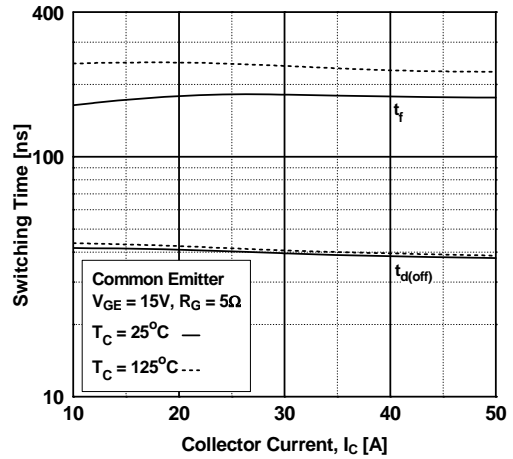


Figure 15. Switching Loss vs. Gate Resistance

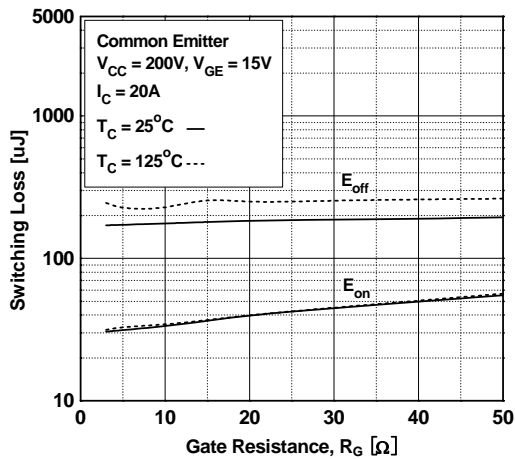


Figure 16. Switching Loss vs. Collector Current

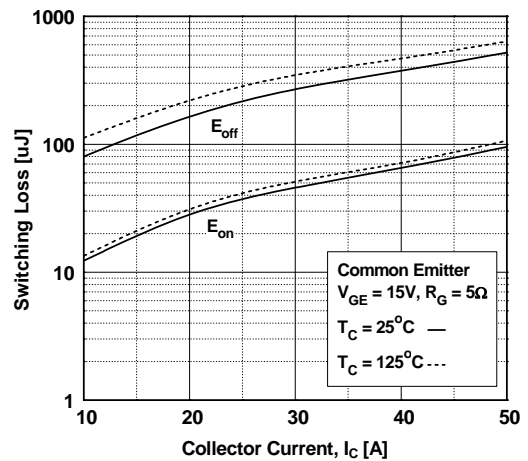
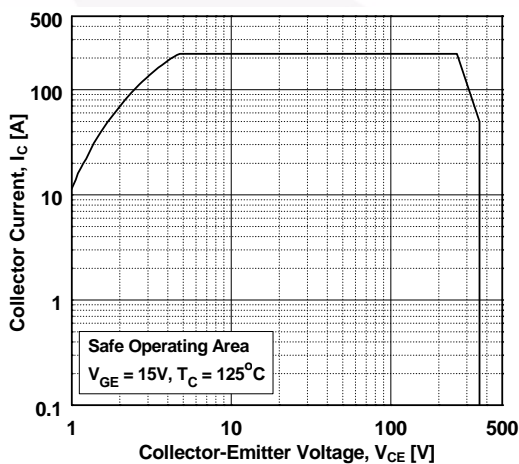
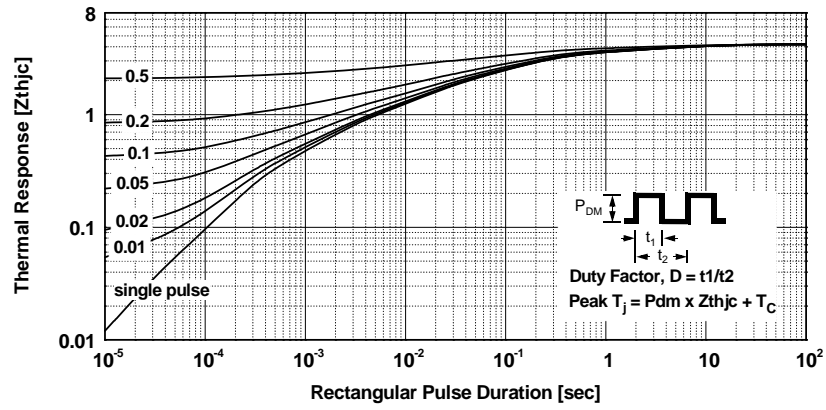


Figure 17. Turn off Switching SOA Characteristics



Typical Performance Characteristics

Figure 18. Transient Thermal Impedance of IGBT



www.fairchildsemi.com